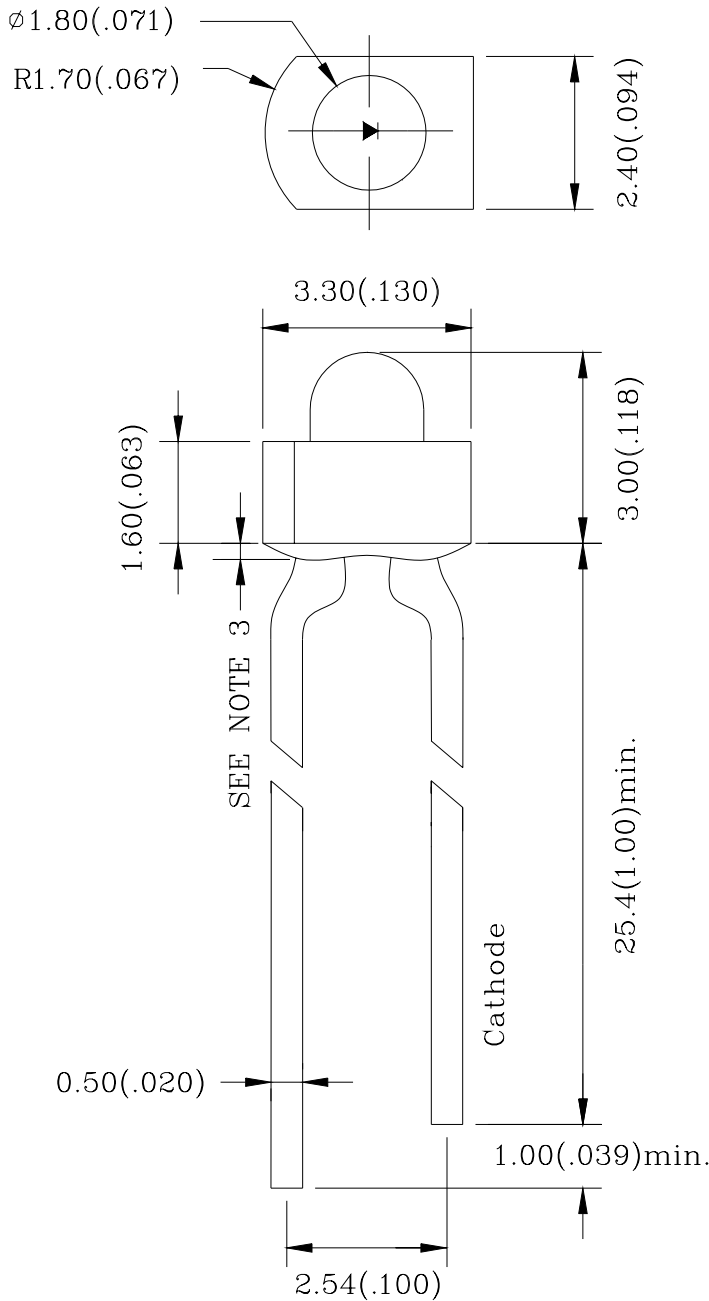


PACKAGE DIMENSIONS



- Note:**
- 1.All Dimensions are in millimeters.
 - 2.Tolerance is $\pm 0.25\text{mm}(0.010\text{ ''})$ Unless otherwise specified.
 - 3.Protruded resin under flange is $1.5\text{mm}(0.059\text{ ''})$ max.
 - 4.Lead spacing is measured where the leads emerge from the package.
 - 5.Specification are subject to change without notice.



1.80 mm DIA TOWER TYPE LED LAMP

HH-1.8YC-35

REV:A / 1

FEATURES

- * 1.8 mm DIA TOWER TYPE LED LAMP
- * HIGH LUMINOUS INTENSITY OUTPUT.
- * LOW POWER CONSUMPTION.
- * HIGH EFFICIENCY.
- * VERSATILE MOUNTING ON P.C. BOARD OR PANEL.
- * I.C. COMPATIBLE.

CHIP MATERIALS

- * Dice Material : GaAlInP
- * Light Color : YELLOW
- * Lens Color : WATER CLEAR

ABSOLUTE MAXIMUM RATING : (Ta = 25°C)

SYMBOL	PARAMETER	ULTRA YELLOW	UNIT
PAD	Power Dissipation Per Chip	80	mW
VR	Reverse Voltage Per Chip	5	V
IAF	Continuous Forward Current Per Chip	30	mA
IPF	Peak Forward Current Per Chip (Duty – 0.1,1KHz)	120	mA
—	Derating Linear From 25°C Per Chip	0.40	mA/°C
Topr	Operating Temperature Range	-25°C to 85°C	
Tstg	Storage Temperature Range	-40°C to 85°C	

Lead Soldering Temperature { 1.6mm(0.063 inch) From Body } 260°C ± 5°C for 5 Seconds

ELECTRO-OPTICAL CHARACTERISTICS : (Ta = 25°C)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V _F	Forward Voltage	I _F = 20mA		2.2		V
I _R	Reverse Current	V _R = 5V			100	μA
λ _D	Dominant Wavelength	I _F = 20mA		589		nm
Δλ	Spectral Line Half-Width	I _F = 20mA		15		nm
2θ _{1/2}	Half Intensity Angle	I _F = 20mA		35		deg
I _V	Luminous Intensity	I _F = 20mA		2250		mcd

